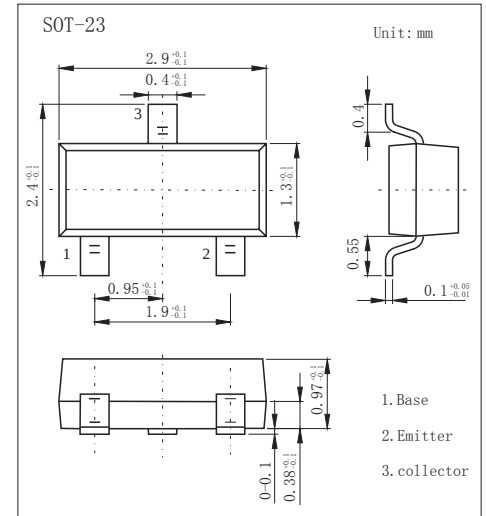


SOT-23 Plastic-Encapsulate Transistors
Features

- Collector Current: $I_C=-1.5A$
- PNP Transistors

MECHANICAL DATA

- Case style:SOT-23 molded plastic
- Mounting position:any


MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-1.5	A
Collector Power Dissipation	P_C	0.3	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to 150	°C

Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C=-100\mu A, I_E=0$	-40			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C=-1mA, I_B=0$	-25			V
Emitter-base breakdown voltage	V_{EBO}	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40V, I_E=0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-20V, I_B=0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-1V, I_C=-100mA$	120		400	
		$V_{CE}=-1V, I_C=-800mA$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-800mA, I_B=-80mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-800mA, I_B=-80mA$			-1.2	V
Base-emitter on voltage	$V_{BE(on)}$	$I_C=-1V, V_{CE}=-10mA$			-1	V
output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$			20	pF
Transition frequency	f_T	$V_{CE}=-10V, I_C=-50mA, f=30MHz$	100			MHz

hFE(1) Classification

Type	SS8550	SS8550-L	SS8550-H	SS8550-J
Range	200-350	120-200	144-202	300-400
Marking	Y2			



RATINGS AND CHARACTERISTIC CURVES

■ Typical Characteristics

